


remove the improper multiple dependent claims.

Examination on the merits is awaited.

Respectfully submitted,

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By:  2002/

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a contact portion for pressing and fixing the peripheral portion of the object to be processed is provided at a lower surface of the inner peripheral portion of the gap-forming member.

3. A [manufacturing] film-forming unit [of a semiconductor device] according to claim 2, wherein:

the gap-forming member is vertically movable.

4. A [manufacturing] film-forming unit [of a semiconductor device] according to claim 2, wherein:

a plurality of contact portions are provided at a predetermined height.

5. A [manufacturing] film-forming unit [of a semiconductor device] according to any of claims 1 to 4, wherein:

a height of the gap defined by the division wall and the outer peripheral portion of the gap-forming member is larger than a height of the gap defined by the peripheral portion of the object to be processed and the inner peripheral portion of the gap-forming member.

6. A [manufacturing] film-forming unit [of a semiconductor device] according to claim 5, wherein:

the height of the gap defined by the division wall and the outer peripheral portion of the gap-forming member is about ten times as large as the height of the gap defined by the peripheral portion of the object to be processed and the inner peripheral portion of the gap-forming member.

7. A [manufacturing] film-forming unit [of a semiconductor device] according to any of claims 1 to [6] 4, wherein:

a temperature controlling means for setting a temperature of the processing container to be higher than a condensation temperature of the process gas and lower than a decomposition temperature and a reaction temperature of the process gas is provided for the processing container.

8. A [manufacturing] film-forming unit [of a semiconductor device] according to any of claims 1 to [7] 4, wherein:

a temperature controlling means for setting a temperature of the process-gas supplying means to be higher than a condensation temperature of the process gas and lower than a decomposition temperature and a reaction temperature of the process gas is provided for the process-gas supplying means.

9. A [manufacturing] film-forming unit [of a semiconductor device] according to any of claims 1 to [8] 4, wherein:

an electrostatic chuck is provided in the stage in order to fix the object to be processed placed on the stage.

10. A [manufacturing] film-forming unit [of a semiconductor device] according to any of claims 1 to [9] 4, wherein:

the gap-forming member is provided with a heater.

11. A [manufacturing] film-forming unit [of a semiconductor device] according to claim 10, wherein:

the gap-forming member is provided with a thermocouple.